

ABSTRACT

A method for producing semiconductor wafers, from a semiconductor ingot, wherein an oxygen concentration distribution in the growth axis direction is measured in the ingot state (F2), a position at which the oxygen concentration is maximum or minimum in a range of a predetermined length is determined as a cut position according to the measurement results (F3), the ingot is cut in a perpendicular direction to the growth axis at the cut position into blocks each having the oxygen concentrations being maximum and minimum at both ends thereof (F4), each of the blocks is sliced, and thereby semiconductor wafers are produced. Thereby, there can be provided a technique by which when semiconductor wafers are produced from a semiconductor ingot, wafers having oxygen concentration being in a predetermined standard range can be certainly produced.